

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of claims:

Claim 1 (currently amended). A test structure for determining a short circuit between trench capacitors in a memory cell array wherein the trench capacitors are arranged in matrix form, the test structure comprising:

at least one of tunnel structures and bridge structures connecting the trench capacitors of two rows of trench capacitors to one another to form trench capacitor rows; ~~and~~

a contact area for contact connection provided at each end section of each of said trench capacitor rows; and

at least one further row of non-connected trench capacitors disposed between said two rows of interconnected trench capacitors.

Claim 2 (original). The test structure according to claim 1, wherein said two rows of interconnected trench capacitors are formed within a regular trench capacitor matrix.

Claim 3 (cancelled).

Claim 4 (new). The test structure according to claim 1,
wherein the test structure is formed in a kerf region of a
wafer.